

Complementary Silicon Power Transistors

MJE270G (NPN), MJE271G (PNP)

Features

- High Safe Operating Area
 $I_{S/B} @ 40 \text{ V}, 1.0 \text{ s} = 0.375 \text{ A}$
- Collector–Emitter Sustaining Voltage
 $V_{CEO(sus)} = 100 \text{ Vdc (Min)}$
- High DC Current Gain
 $h_{FE} @ 120 \text{ mA}, 10 \text{ V} = 1500 \text{ (Min)}$
- These Devices are Pb–Free and are RoHS Compliant

MAXIMUM RATINGS

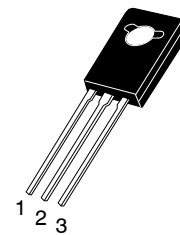
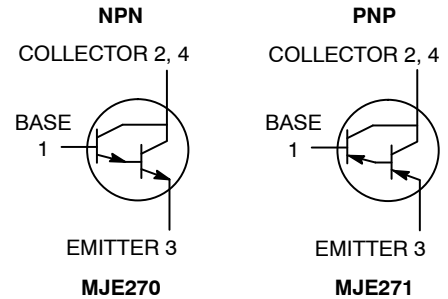
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	100	Vdc
Collector–Base Voltage	V_{CB}	100	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous	I_C	2.0	Adc
Collector Current – Peak	I_{CM}	4.0	Adc
Base Current	I_B	0.1	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 0.012	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

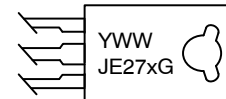
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	8.33	$^\circ\text{C/W}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	83.3	$^\circ\text{C/W}$

2.0 AMPERE COMPLEMENTARY POWER DARLINGTON TRANSISTORS 100 VOLTS, 15 WATTS



TO–225
CASE 77–09
STYLE 3

MARKING DIAGRAM



- Y = Year
 WW = Work Week
 JE27x = Specific Device Code
 x = 0 or 1
 G = Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping†
MJE270G	TO–225 (Pb–Free)	500 Units / Box
MJE270TG	TO–225 (Pb–Free)	50 Units / Box

DISCONTINUED (Note 1)

MJE271G	TO–225 (Pb–Free)	500 Units / Box
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†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

MJE270G (NPN), MJE271G (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 2) (I _C = 10 mAdc, I _B = 0)	V _{CEO(sus)}	100	-	Vdc
Collector Cutoff Current (V _{CE} = 100 Vdc, I _B = 0)	I _{CEO}	-	1.0	mAdc
Collector Cutoff Current (V _{CB} = 100 Vdc, I _E = 0)	I _{CBO}	-	0.3	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	0.1	mAdc

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 40 Vdc, t = 1.0 s, Non-repetitive)	I _{S/b}	375	-	Adc
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ON CHARACTERISTICS (Note 2)

DC Current Gain (I _C = 20 mAdc, V _{CE} = 3.0 Vdc) (I _C = 120 mAdc, V _{CE} = 10 Vdc)	h _{FE}	500 1500	- -	-
Collector-Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 0.2 mAdc) (I _C = 120 mAdc, I _B = 1.2 mAdc)	V _{CE(sat)}	- -	2.0 3.0	Vdc
Base-Emitter On Voltage (I _C = 120 mAdc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	2.0	Vdc

DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product (Note 3) (I _C = 0.05 Adc, V _{CE} = 5.0 Vdc, f _{test} = 1.0 MHz)	f _T	6.0	-	MHz
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
- f_T = |h_{fe}| • f_{test}.

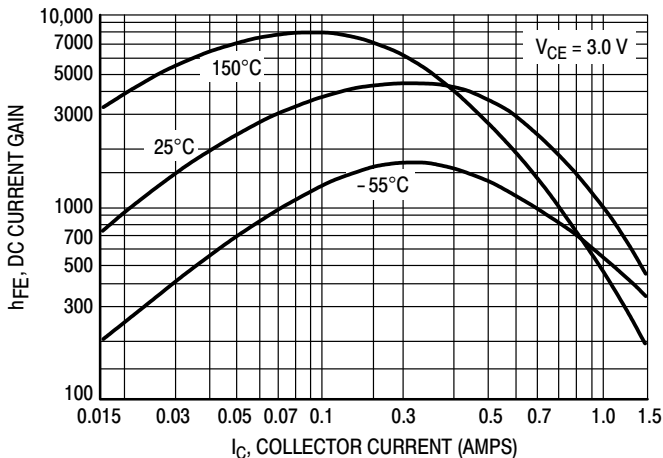


Figure 1. DC Current Gain

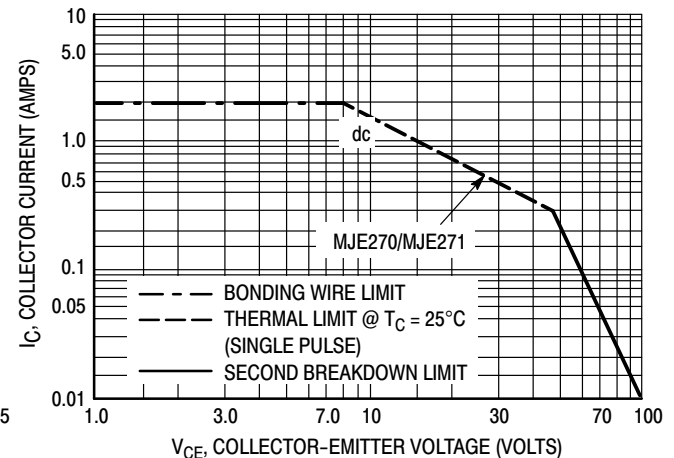
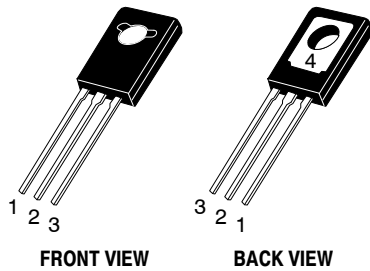


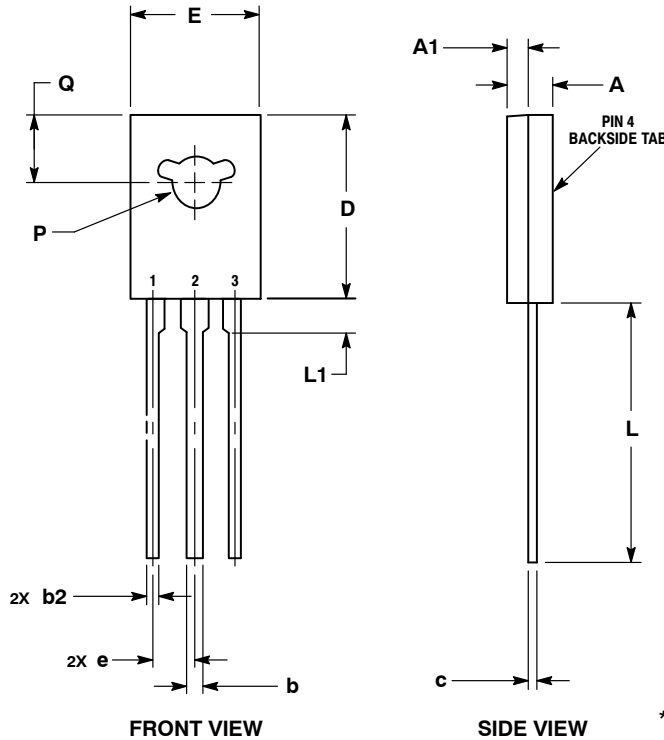
Figure 2. Safe Operating Area



TO-225
CASE 77-09
ISSUE AD

DATE 25 MAR 2015

SCALE 1:1

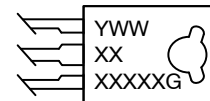


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. NUMBER AND SHAPE OF LUGS OPTIONAL.

DIM	MILLIMETERS	
	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

GENERIC MARKING DIAGRAM*



- Y = Year
- WW = Work Week
- XXXXX = Device Code
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present. Some products may not follow the Generic Marking.

<p>STYLE 1: PIN 1. EMITTER 2., 4. COLLECTOR 3. BASE</p>	<p>STYLE 2: PIN 1. CATHODE 2., 4. ANODE 3. GATE</p>	<p>STYLE 3: PIN 1. BASE 2., 4. COLLECTOR 3. EMITTER</p>	<p>STYLE 4: PIN 1. ANODE 1 2., 4. ANODE 2 3. GATE</p>	<p>STYLE 5: PIN 1. MT 1 2., 4. MT 2 3. GATE</p>
<p>STYLE 6: PIN 1. CATHODE 2., 4. GATE 3. ANODE</p>	<p>STYLE 7: PIN 1. MT 1 2., 4. GATE 3. MT 2</p>	<p>STYLE 8: PIN 1. SOURCE 2., 4. GATE 3. DRAIN</p>	<p>STYLE 9: PIN 1. GATE 2., 4. DRAIN 3. SOURCE</p>	<p>STYLE 10: PIN 1. SOURCE 2., 4. DRAIN 3. GATE</p>

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